



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

SOT-563 Plastic-Encapsulate Transistors

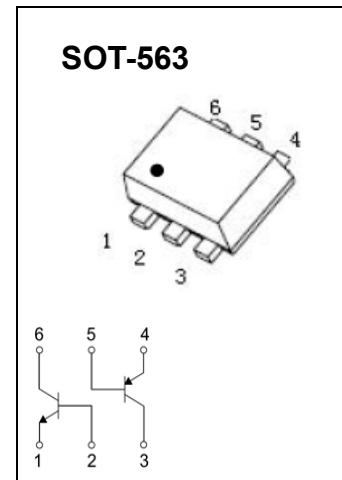
NST3946 DUAL TRANSISTOR (PNP+NPN)

DESCRIPTION

It is designed for general purpose amplifier applications . By putting two Discrete devices in one package , this device is ideal for low – power surface mount applications where board space is at a premium.

FEATURES

- Low $V_{CE(sat)}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count



Marking: 46

PNP 3906 Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-200	mA
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.05	μA
DC current gain	h_{FE}	$V_{CE}=-1\text{V}, I_C=-0.1\text{mA}$	60			
		$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	80			
		$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100		300	
		$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	60			
		$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.25	V
		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.4	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$	-0.65		-0.85	V
		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.95	V
Transition frequency	f_T	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	250			MHz
Output capacitance	C_{ob}	$V_{CB}=-5\text{V}, I_E=0, f=1\text{MHz}$			4.5	pF

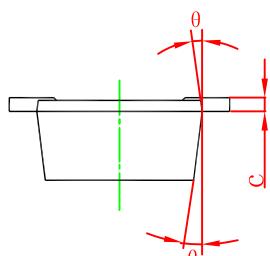
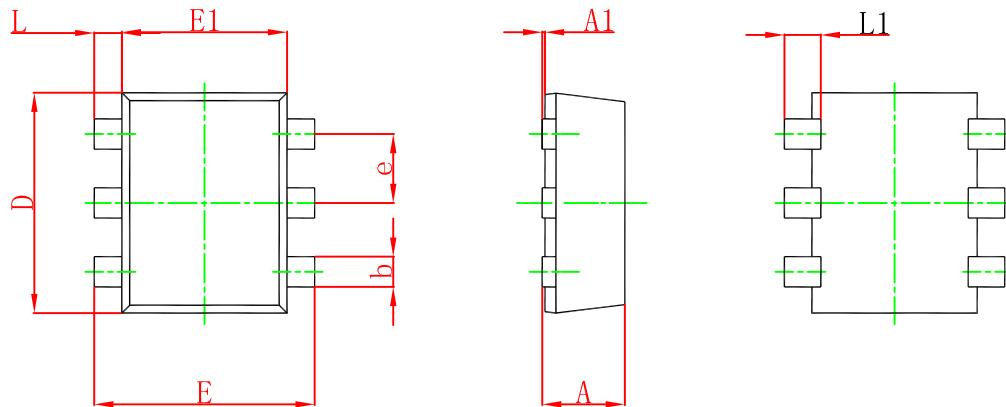
NPN 3904 Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

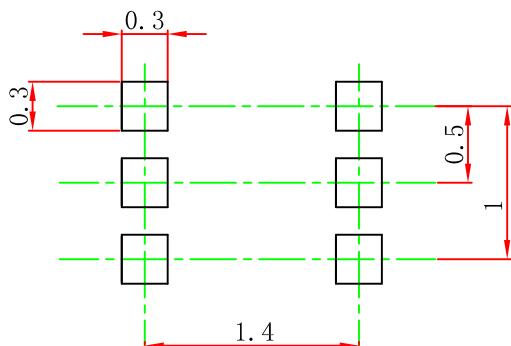
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.05	μA
DC current gain	h_{FE}	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
		$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
		$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
		$V_{CE}=-1\text{V}, I_C=50\text{mA}$	60			
		$V_{CE}=-1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	300			MHz
Output capacitance	C_{ob}	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$			4	pF

SOT-563 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7° REF.		7° REF.	

SOT-563 Suggested Pad Layout



Note:

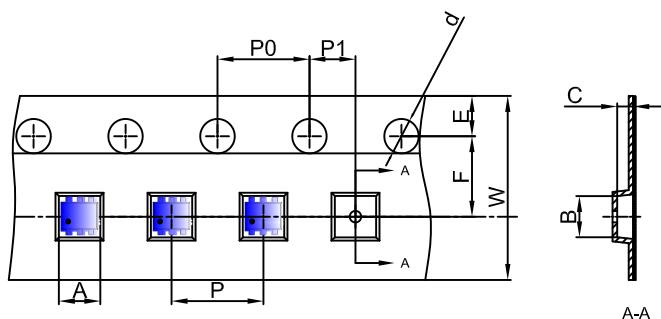
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

SOT-563 Tape and Reel

SOT-563 Embossed Carrier Tape

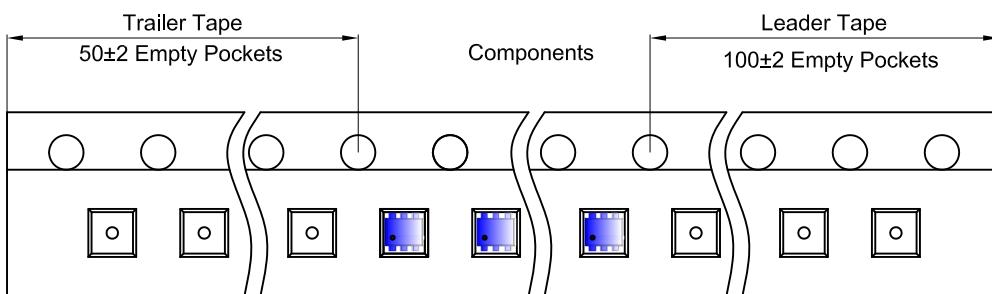


Packaging Description:

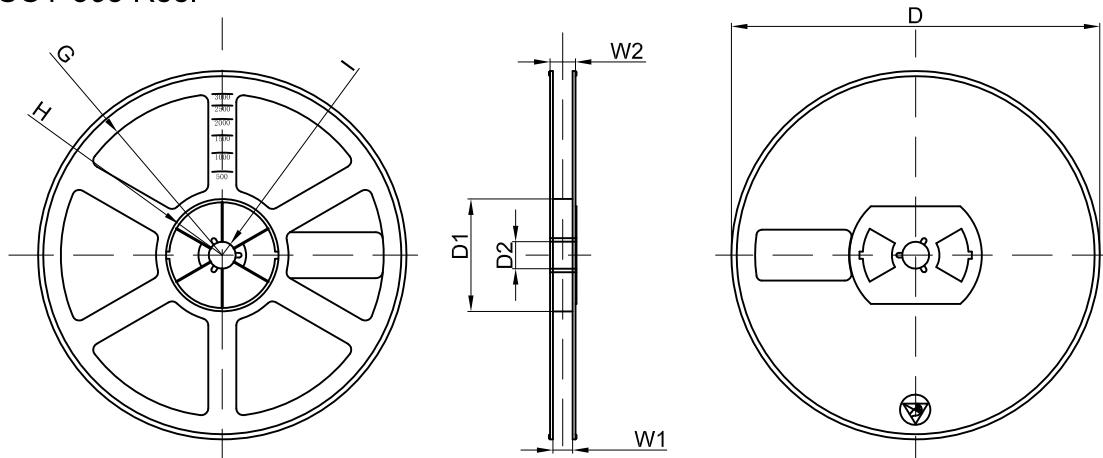
SOT-563 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-563	1.78	1.78	0.69	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-563 Tape Leader and Trailer



SOT-563 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	